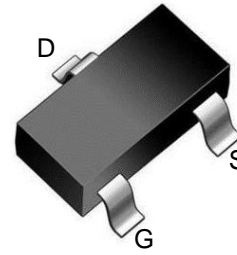


-40V P-Channel MOSFET

Features

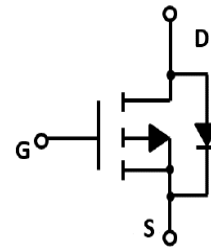
- High density cell design for ultra low $R_{DS(ON)}$
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation



SOT-23 top view

Application

- Power switching application
- Hard switched and high frequency circuits
- DC-DC converter



Schematic diagram

Product Summary

V_{DS}	$R_{DS(ON)}$ MAX	I_D MAX
-40V	90m Ω @-10V	-4.4A
	150m Ω @-4.5V	

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)				
Symbol	Parameter		Rating	Unit
Common Ratings ($T_C=25^\circ\text{C}$ Unless Otherwise Noted)				
V_{DS}	Drain-Source Breakdown Voltage		-40	V
V_{GS}	Gate-Source Voltage		± 20	V
T_J	Maximum Junction Temperature		150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range		-55 to 150	$^\circ\text{C}$
I_S	Diode Continuous Forward Current	$T_C=25^\circ\text{C}$	-4	A
Mounted on Large Heat Sink				
I_{DM}	Pulse Drain Current Tested	$T_C=25^\circ\text{C}$	-15	A
I_D	Continuous Drain Current@GS=10V	$T_C=25^\circ\text{C}$	-4.4	A
P_D	Maximum Power Dissipation	$T_C=25^\circ\text{C}$	1.2	W
$R_{\theta JA}$	Thermal Resistance Junction-to-Ambient		104	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25°C unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
B _{V(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-40	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-40V, V _{GS} =0V	--	--	-1	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1.0	-1.8	-2.5	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =-10V, I _D =-2A	--	77	90	mΩ
		V _{GS} =-4.5V, I _D =-1A	--	115	150	mΩ
Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =-20V, V _{GS} =0V, f=1MHz	--	600	--	pF
C _{OSS}	Output Capacitance		--	90	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	70	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DS} =-20V, I _D =-3A, V _{GS} =-10V	--	14	--	nC
Q _{gs}	Gate Source Charge		--	3	--	nC
Q _{gd}	Gate Drain Charge		--	3.8	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =-20V, I _D =-3A, V _{GS} =-10V, R _G =3Ω	--	9	--	nS
t _r	Turn-on Rise Time		--	8	--	nS
t _{d(off)}	Turn-Off Delay Time		--	28	--	nS
t _f	Turn-Off Fall Time		--	11	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	T _J =25°C, I _S =-4A,	--	--	-1.2	V

Typical Operating Characteristics

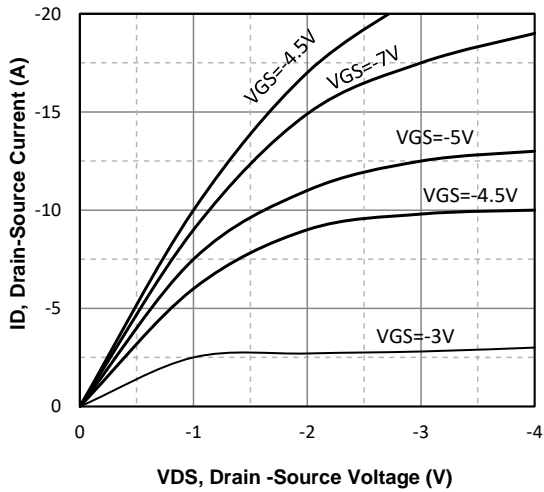


Fig1. Typical Output Characteristics

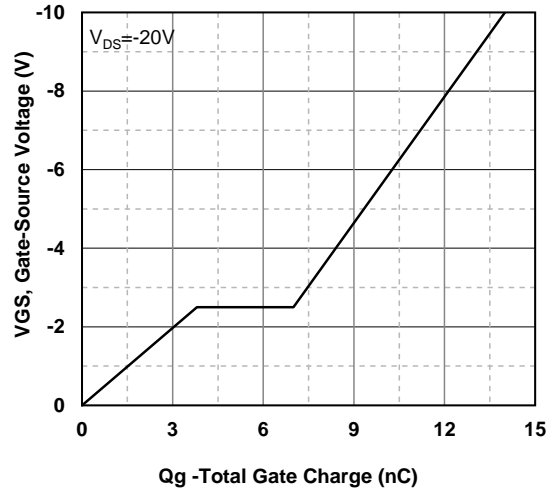


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

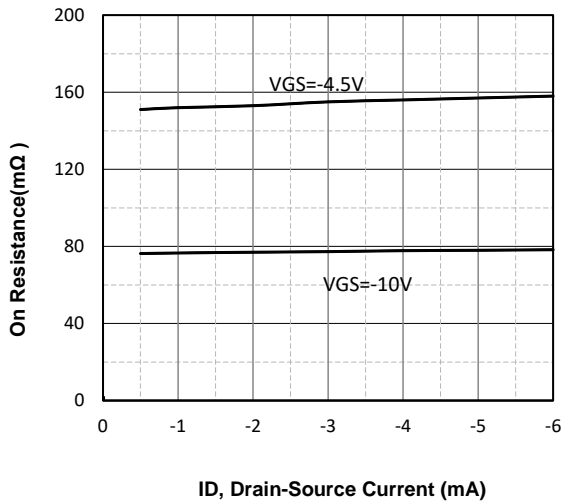


Fig3. Drain-Source on Resistance

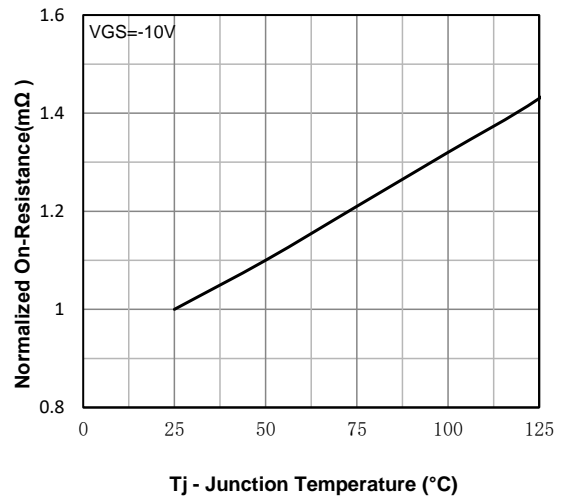


Fig4. Normalized On-Resistance Vs. Temperature

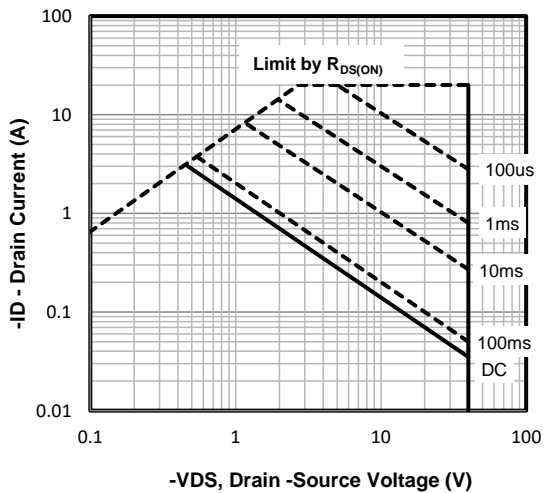


Fig5. Maximum Safe Operating Area

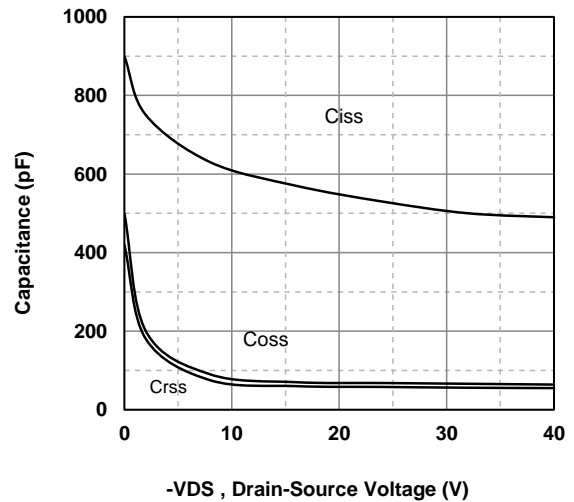
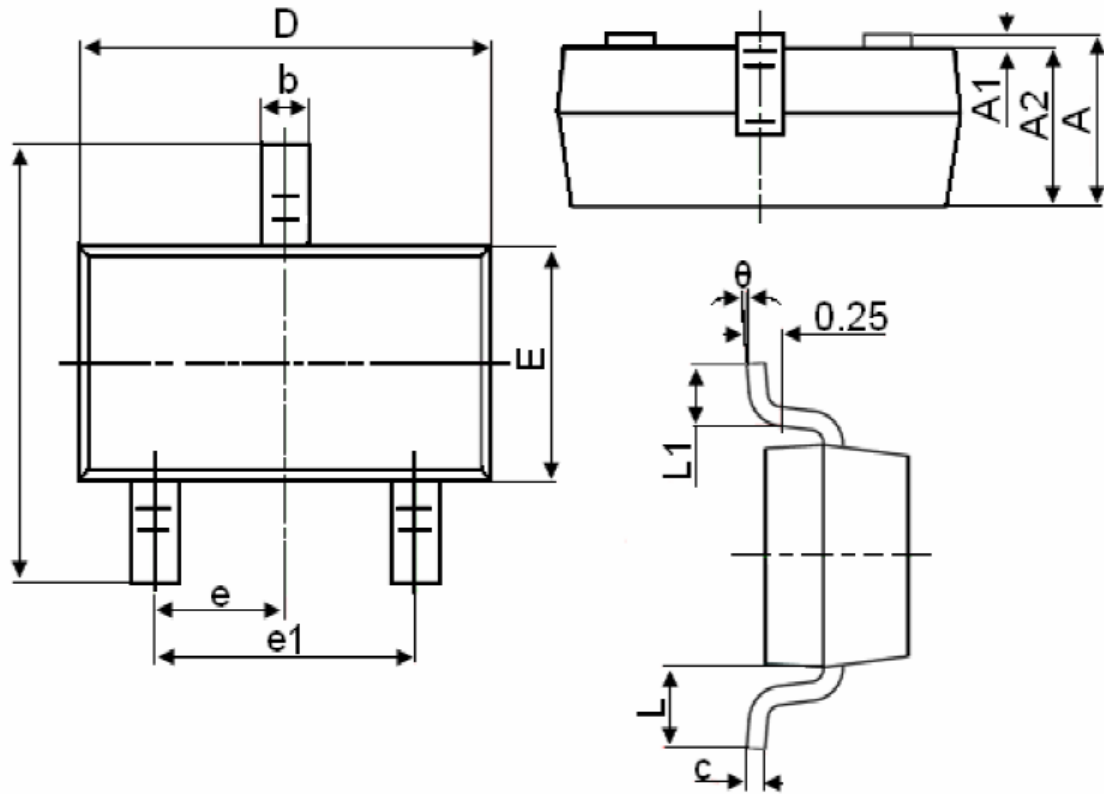


Fig6 Typical Capacitance Vs. Drain-Source Voltage

SOT-23 Package information


Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°